

AUIRGR4045D

AUIRGU4045D

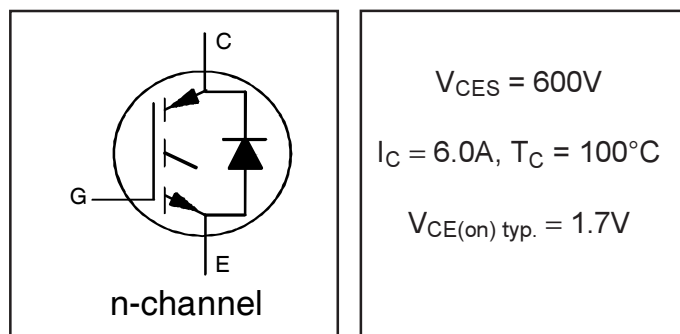
INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

Features

- Low $V_{CE(on)}$ Trench IGBT Technology
- Low Switching Losses
- Maximum Junction temperature 175 °C
- 5μs SCSOA
- Square RBSOA
- 100% of the parts tested for I_{LM} ①
- Positive $V_{CE(on)}$ Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Tighter Distribution of Parameters
- Lead-Free, RoHS Compliant
- Automotive Qualified*

Benefits

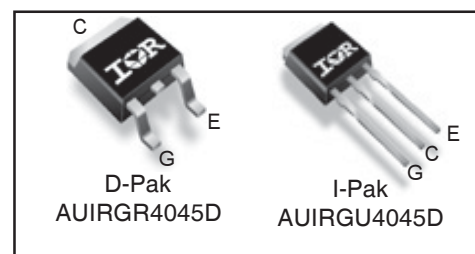
- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low $V_{CE(ON)}$ and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI



$$V_{CES} = 600V$$

$$I_C = 6.0A, T_C = 100^{\circ}C$$

$$V_{CE(on) typ.} = 1.7V$$



G	C	E
Gate	Collector	Emitter

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V _{CES}	Collector-to-Emitter Breakdown Voltage	600	V
I _C @ T _C = 25°C	Continuous Collector Current	12	A
I _C @ T _C = 100°C	Continuous Collector Current	6.0	
I _{CM}	Pulsed Collector Current, V _{GE} = 15V	18	
I _{LM}	Clamped Inductive Load Current, V _{GE} = 20V ①	24	
I _F @T _C =25°C	Diode Continuous Forward Current	8.0	
I _F @T _C =100°C	Diode Continuous Forward Current	4.0	
I _{FM}	Diode Maximum Forward Current ②	24	
V _{GE}	Continuous Gate-to-Emitter Voltage	± 20	V
	Transient Gate-to-Emitter Voltage	± 30	
P _D @ T _C =25°	Maximum Power Dissipation	77	W
P _D @ T _C =100°	Maximum Power Dissipation	39	
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT ③	—	—	1.9	°C/W
$R_{\theta JC}$	Junction-to-Case - Diode ③	—	—	6.8	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑤	—	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	—	110	

*Qualification standards can be found at <http://www.irf.com/>

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 100\mu A$ ④	CT6
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.36	—	V/°C	$V_{GE} = 0V, I_C = 250\mu A$ (25 -175 °C) ④	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.7	2.0	V	$I_C = 6.0A, V_{GE} = 15V, T_J = 25^\circ\text{C}$	5,6,7,9, 10,11
		—	2.07	—		$I_C = 6.0A, V_{GE} = 15V, T_J = 150^\circ\text{C}$	
		—	2.14	—		$I_C = 6.0A, V_{GE} = 15V, T_J = 175^\circ\text{C}$	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	—	6.5	V	$V_{CE} = V_{GE}, I_C = 150\mu A$	9,10,11,12
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-13	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$ (25 -175 °C)	
g_{fe}	Forward Transconductance	—	5.8	—	S	$V_{CE} = 25V, I_C = 6.0A, PW = 80\mu s$	
I_{CES}	Collector-to-Emitter Leakage Current	—	—	25	μA	$V_{GE} = 0V, V_{CE} = 600V$	8
		—	—	250		$V_{GE} = 0V, V_{CE} = 600V, T_J = 175^\circ\text{C}$	
V_{FM}	Diode Forward Voltage Drop	—	1.60	2.30	V	$I_F = 6.0A$	
		—	1.30	—		$I_F = 6.0A, T_J = 175^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
Q_g	Total Gate Charge (turn-on)	—	13	19.5	nC	$I_C = 6.0A$	24 CT1
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	3.1	4.65		$V_{CC} = 400V$	
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	6.4	9.6		$V_{GE} = 15V$	
E_{on}	Turn-On Switching Loss	—	56	86	μJ	$I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$	CT4
E_{off}	Turn-Off Switching Loss	—	122	143		$R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 25^\circ\text{C}$	
E_{total}	Total Switching Loss	—	178	229		Energy losses include tail and diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	27	35	ns	$I_C = 6.0A, V_{CC} = 400V$	CT4
t_r	Rise time	—	11	15		$R_G = 47\Omega, L = 1mH, L_S = 150nH$	
$t_{d(off)}$	Turn-Off delay time	—	75	93		$T_J = 25^\circ\text{C}$	
t_f	Fall time	—	17	22			
E_{on}	Turn-On Switching Loss	—	140	—	μJ	$I_C = 6.0A, V_{CC} = 400V, V_{GE} = 15V$	13,15 CT4 WF1,WF2
E_{off}	Turn-Off Switching Loss	—	189	—		$R_G = 47\Omega, L = 1mH, L_S = 150nH, T_J = 175^\circ\text{C}$	
E_{total}	Total Switching Loss	—	329	—		Energy losses include tail and diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	26	—	ns	$I_C = 6.0A, V_{CC} = 400V$	14,16 CT4 WF1,WF2
t_r	Rise time	—	12	—		$R_G = 47\Omega, L = 1mH, L_S = 150nH$	
$t_{d(off)}$	Turn-Off delay time	—	95	—		$T_J = 175^\circ\text{C}$	
t_f	Fall time	—	32	—			
C_{ies}	Input Capacitance	—	350	—	pF	$V_{GE} = 0V$	23
C_{oes}	Output Capacitance	—	29	—		$V_{CC} = 30V$	
C_{res}	Reverse Transfer Capacitance	—	10	—		$f = 1Mhz$	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				$T_J = 175^\circ\text{C}, I_C = 24A$ $V_{CC} = 500V, V_p = 600V$ $R_G = 100\Omega, V_{GE} = +20V \text{ to } 0V$	4 CT2
SCSOA	Short Circuit Safe Operating Area	—	5	—	μs	$V_{CC} = 400V, V_p = 600V$ $R_G = 100\Omega, V_{GE} = +15V \text{ to } 0V$	22 CT3, WF4
E_{rec}	Reverse recovery energy of the diode	—	178	—	μJ	$T_J = 175^\circ\text{C}$	17,18,19 20,21 WF3
t_{rr}	Diode Reverse recovery time	—	74	—	ns	$V_{CC} = 400V, I_F = 6.0A$	
I_{rr}	Peak Reverse Recovery Current	—	12	—	A	$V_{GE} = 15V, R_G = 47\Omega, L = 1mH, L_S = 150nH$	

Notes:

- ① $V_{CC} = 80\% (V_{CES}), V_{GE} = 15V, L = 1.0mH, R_G = 47\Omega$.
- ② Pulse width limited by max. junction temperature.
- ③ R_θ is measured at T_J approximately 90°C .
- ④ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
- ⑤ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D-Pak	MSL1
		I-PAK	
ESD	Machine Model	Class M2 (+/- 200V) ^{†††} AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1000V) ^{†††} AEC-Q101-005	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com>

^{††} Exceptions to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage.

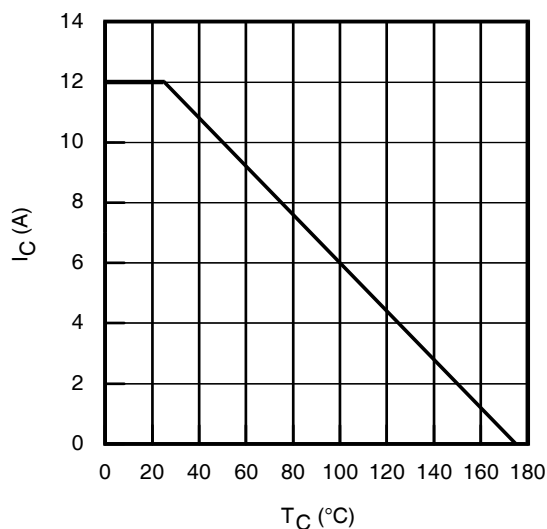


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

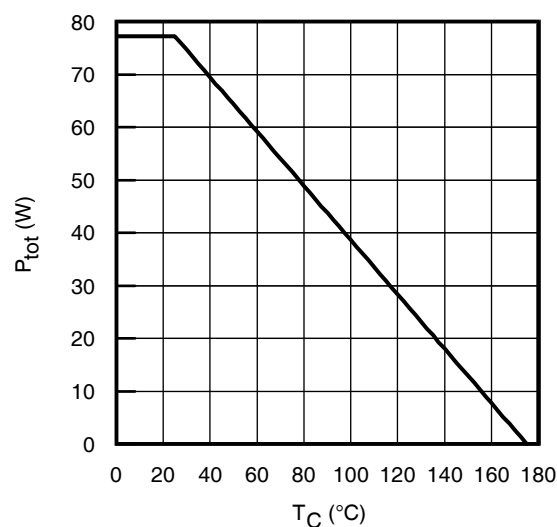


Fig. 2 - Power Dissipation vs. Case Temperature

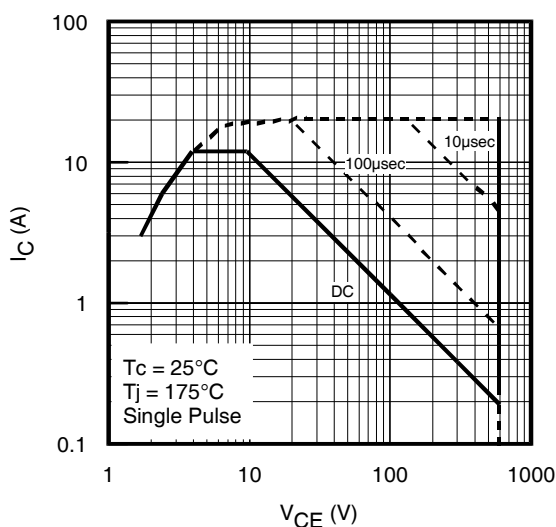


Fig. 3 - Forward SOA,
 $T_C = 25^{\circ}\text{C}$, $T_J \leq 175^{\circ}\text{C}$, $V_{GE} = 15\text{V}$

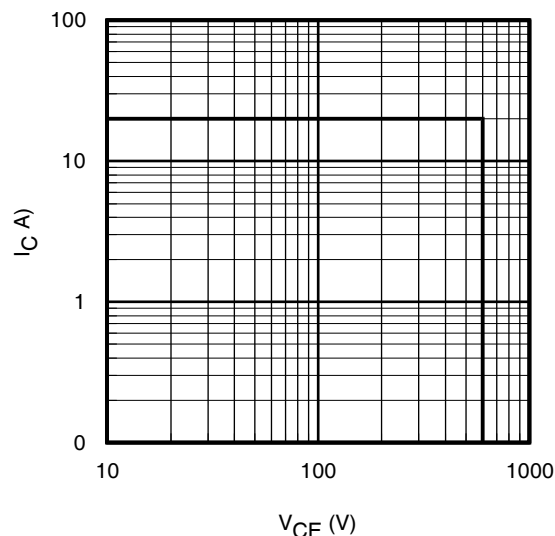


Fig. 4 - Reverse Bias SOA
 $T_J = 175^{\circ}\text{C}$, $V_{GE} = 20\text{V}$

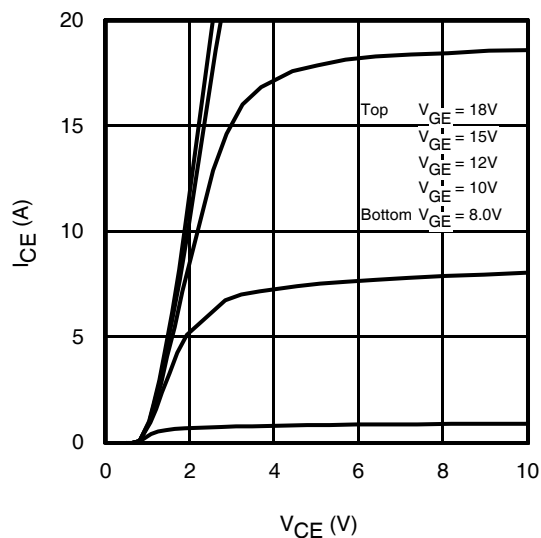


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^{\circ}\text{C}$; $t_p = 80 \mu\text{s}$

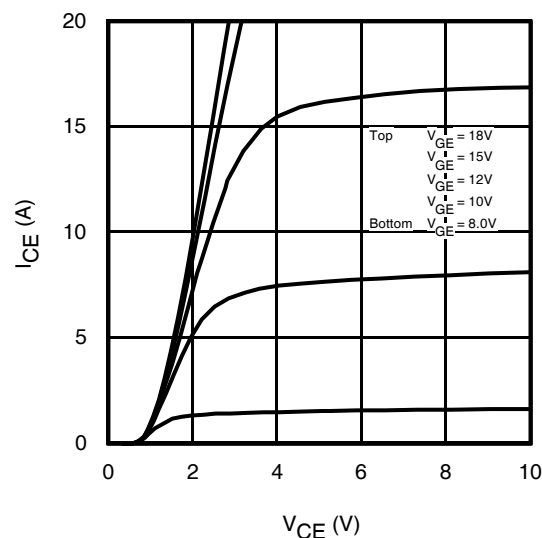


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^{\circ}\text{C}$; $t_p = 80 \mu\text{s}$

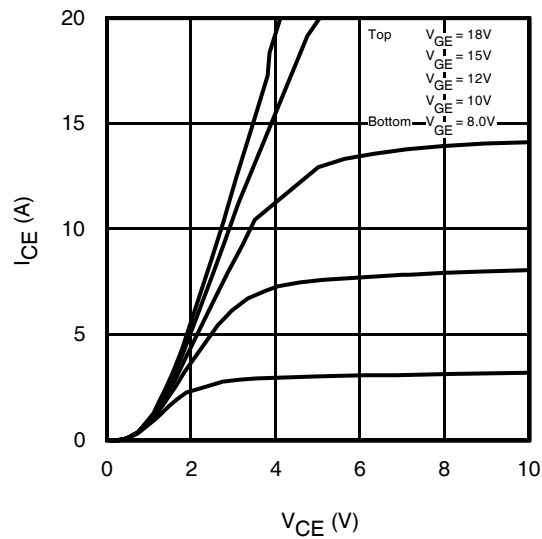


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = 80\mu\text{s}$

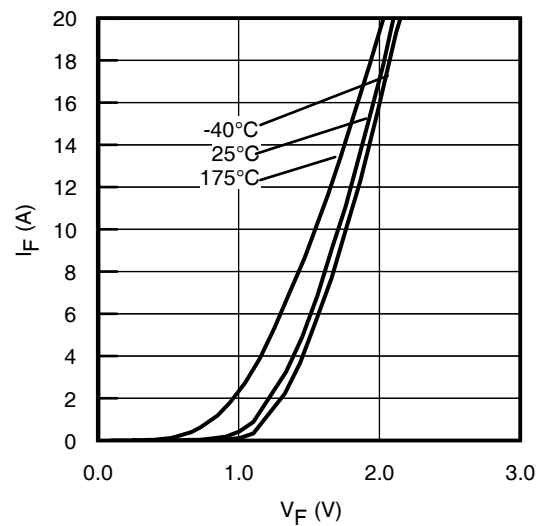


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

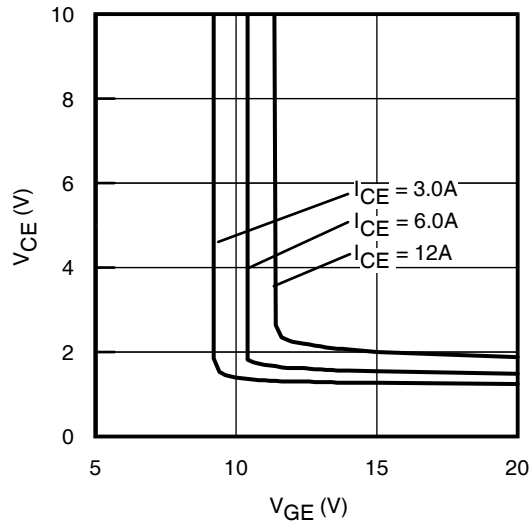


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

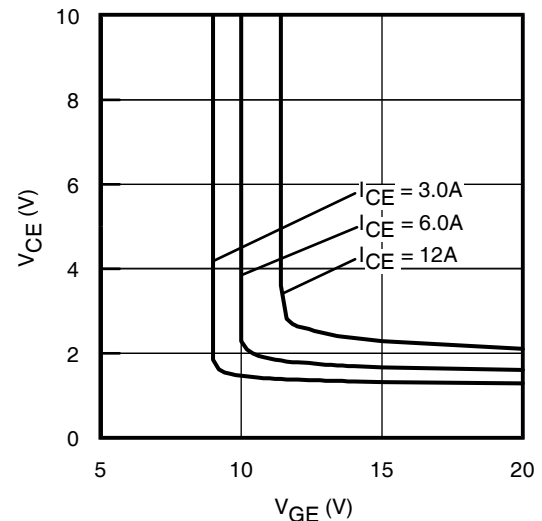


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

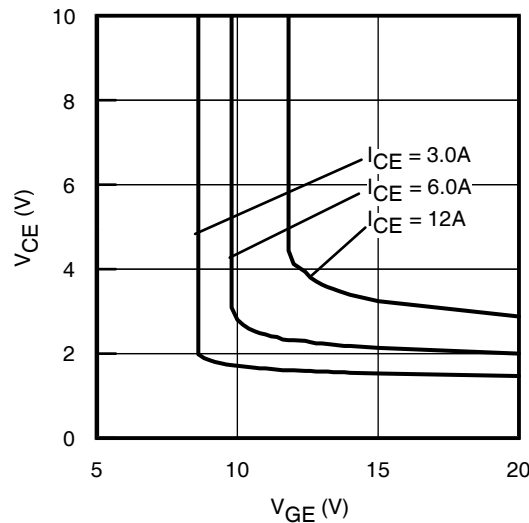


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

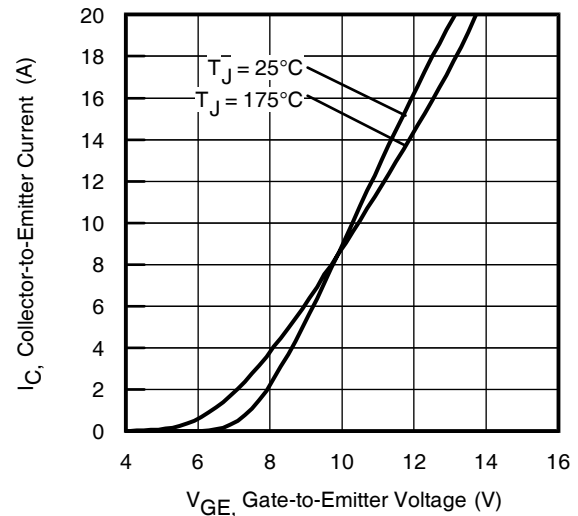


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 10\mu\text{s}$

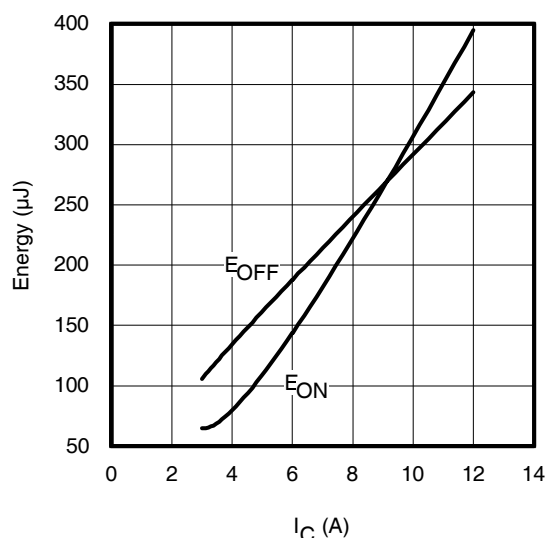


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 1\text{mH}$; $V_{CE} = 400\text{V}$; $R_G = 47\Omega$; $V_{GE} = 15\text{V}$.

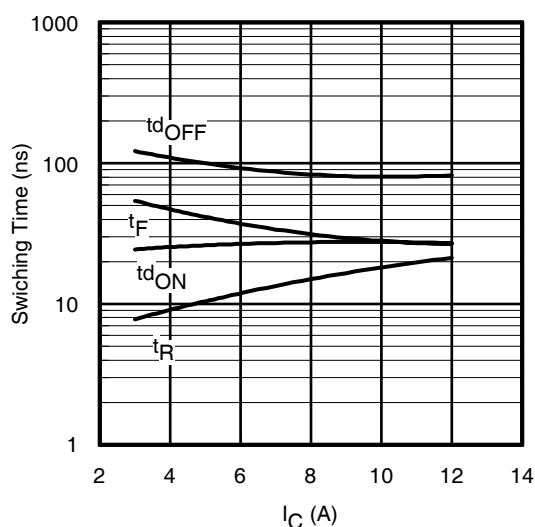


Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}$; $L = 1\text{mH}$; $V_{CE} = 400\text{V}$
 $R_G = 47\Omega$; $V_{GE} = 15\text{V}$

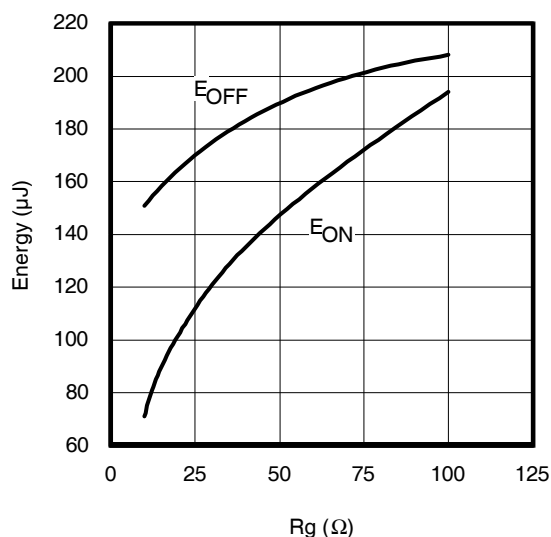


Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 1\text{mH}$; $V_{CE} = 400\text{V}$; $I_{CE} = 6.0\text{A}$; $V_{GE} = 15\text{V}$

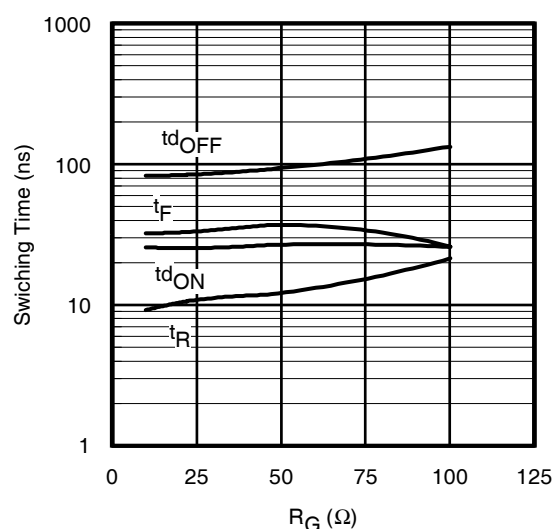


Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}$; $L = 1\text{mH}$; $V_{CE} = 400\text{V}$
 $I_{CE} = 6.0\text{A}$; $V_{GE} = 15\text{V}$

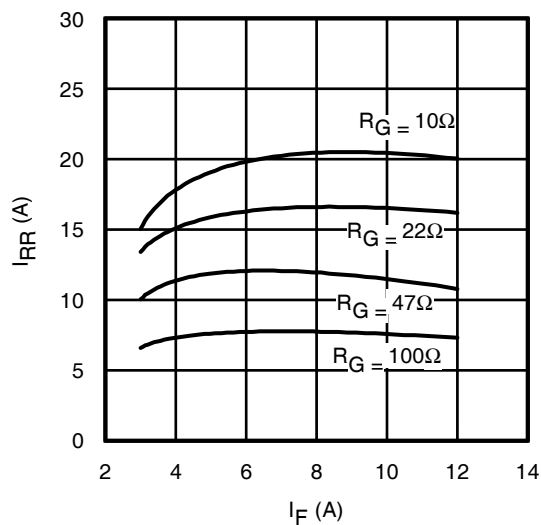


Fig. 17 - Typical Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

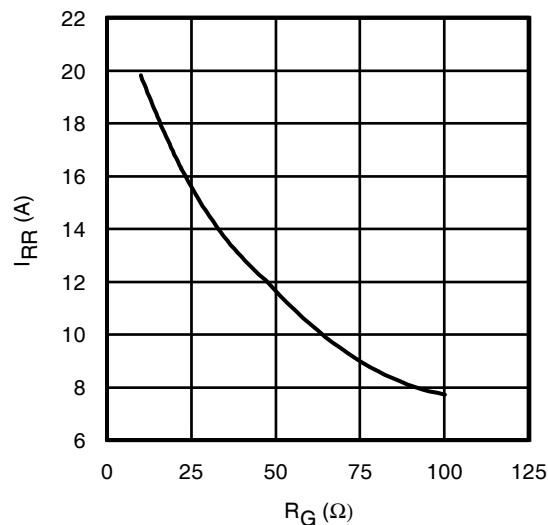


Fig. 18 - Typical Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$; $I_F = 6.0\text{A}$

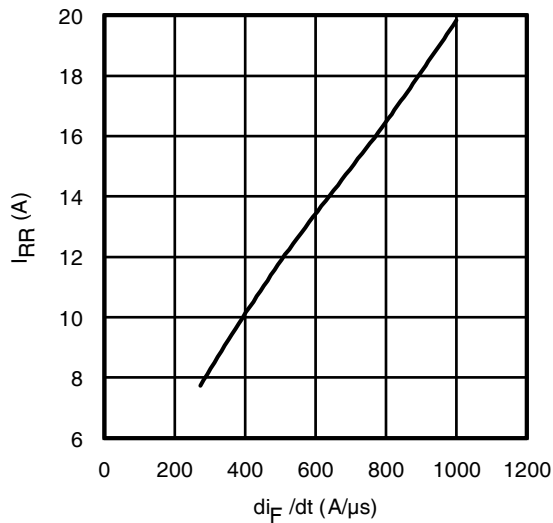


Fig. 19 - Typical Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$;
 $I_{CE} = 6.0A$; $T_J = 175^\circ C$

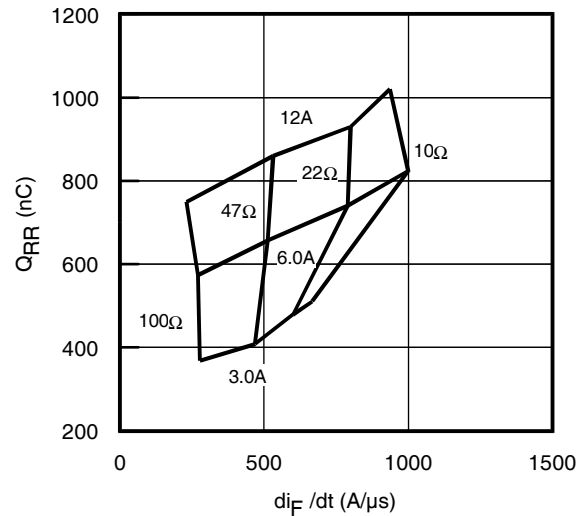


Fig. 20 - Typical Diode Q_{RR}
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

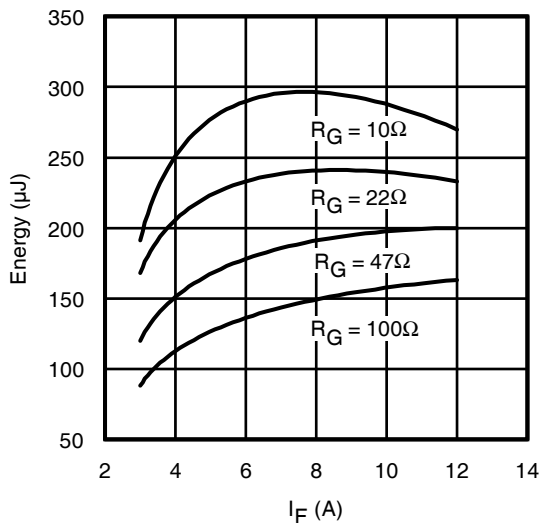


Fig. 21 - Typical Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

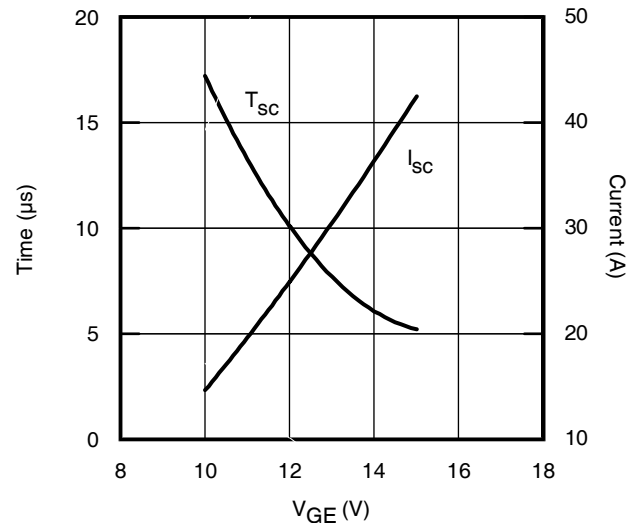


Fig. 22 - Typ. V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$, $T_C = 25^\circ C$

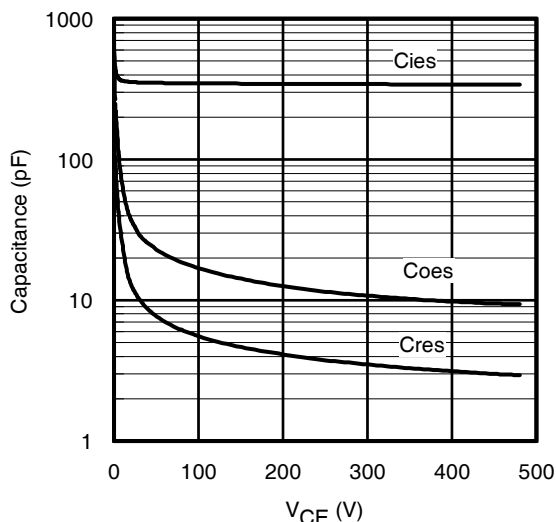


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

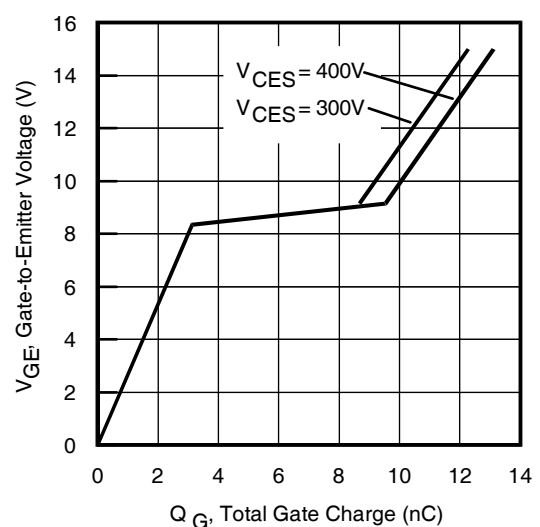


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 6.0A$, $L = 600\mu H$

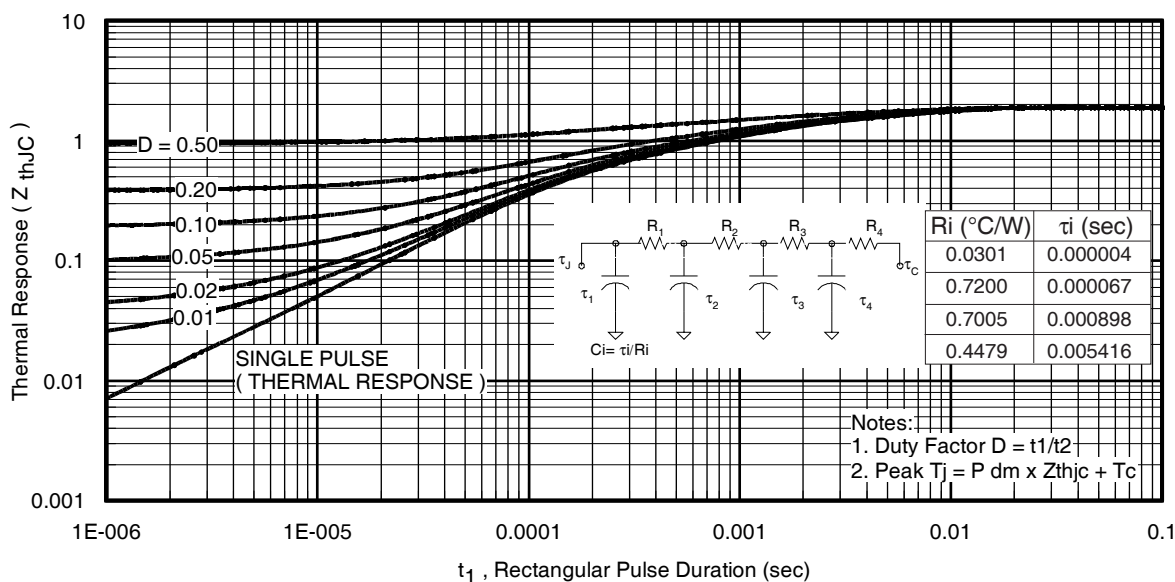


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

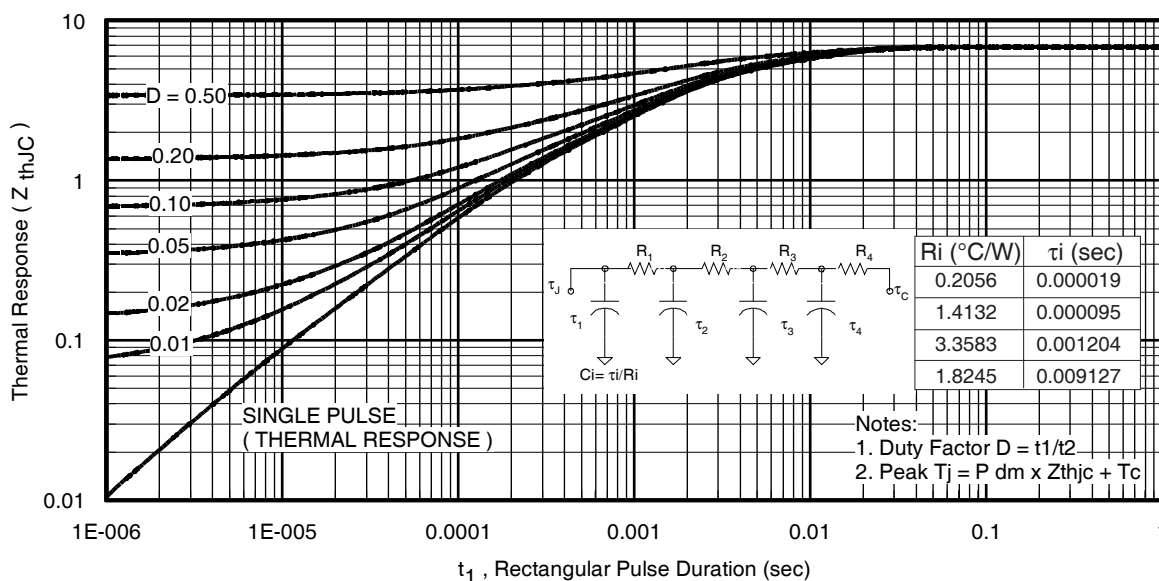


Fig 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

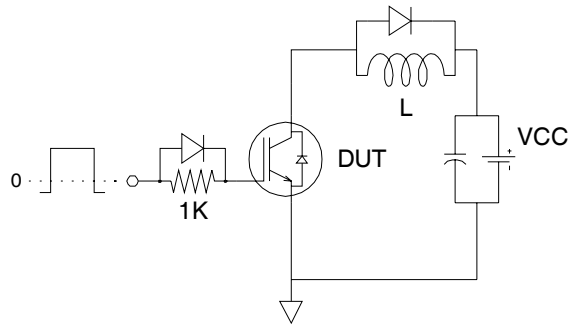


Fig.C.T.1 - Gate Charge Circuit (turn-off)

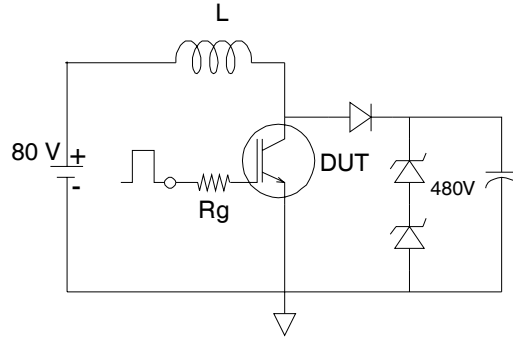


Fig.C.T.2 - RBSOA Circuit

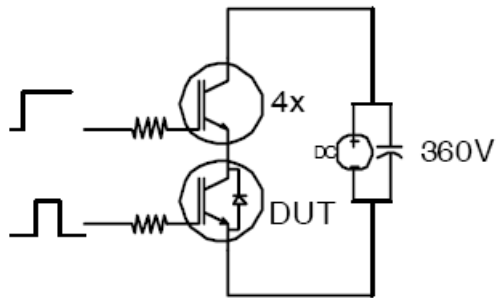


Fig.C.T.3 - S.C.SOA Circuit

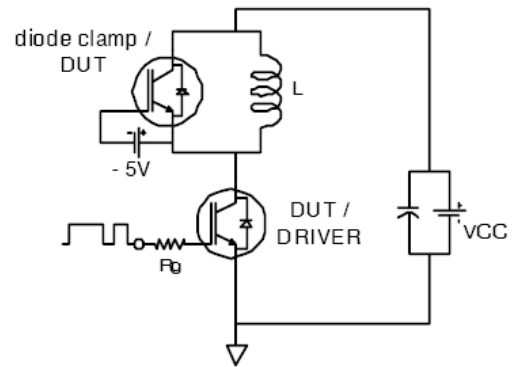


Fig.C.T.4 - Switching Loss Circuit

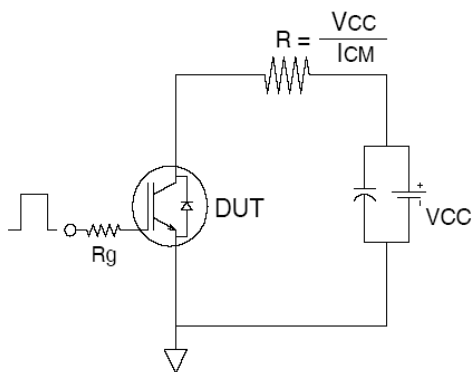


Fig.C.T.5 - Resistive Load Circuit

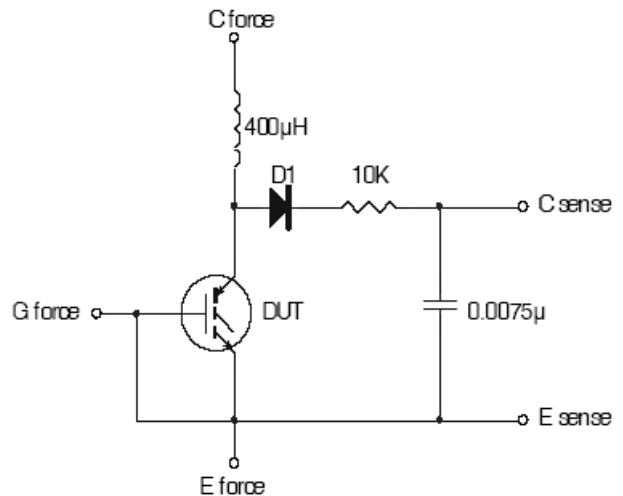


Fig.C.T.6 - Typical Filter Circuit for $V_{(BR)CES}$ Measurement

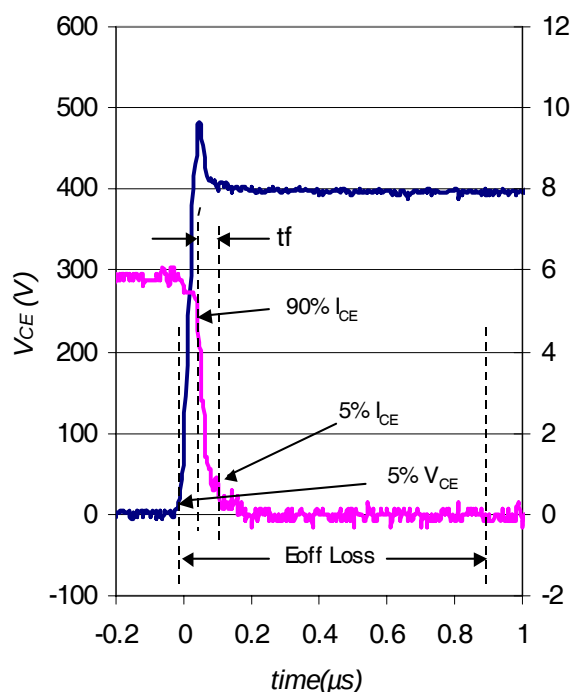


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

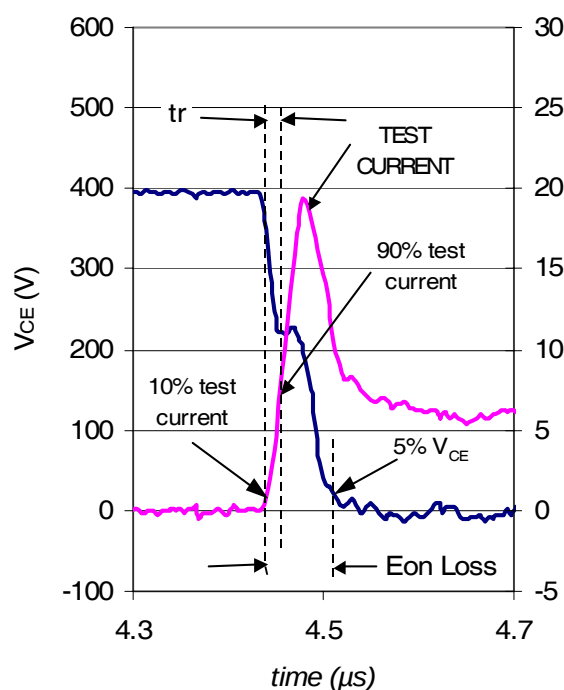
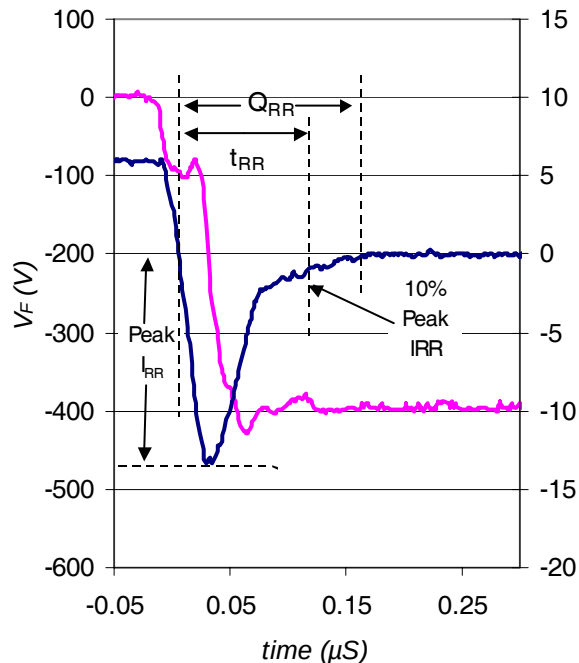
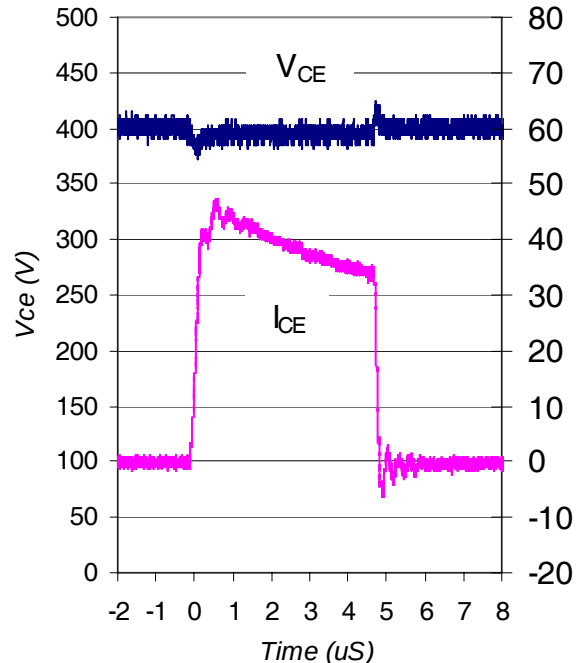


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4



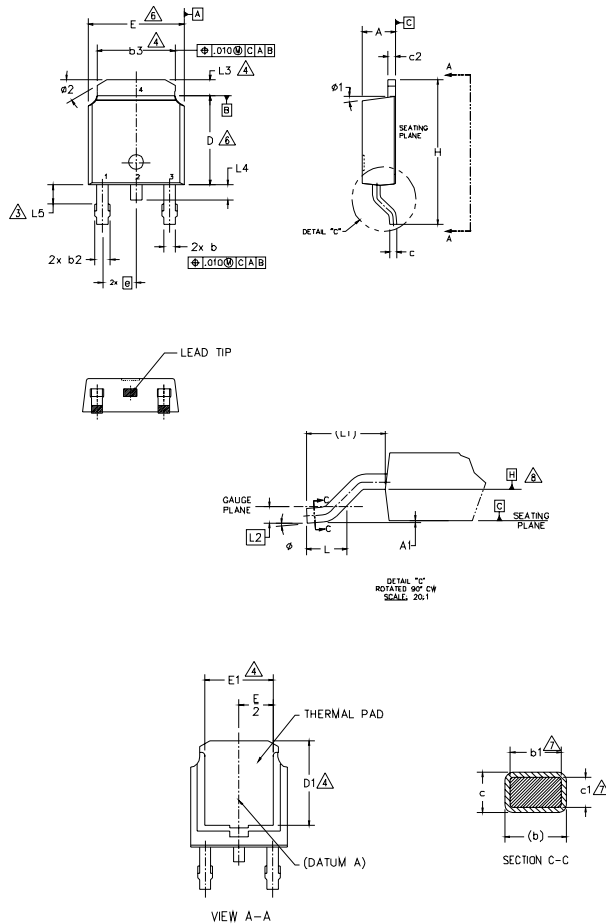
WF.3- Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using CT.4



WF.4- Typ. Short Circuit Waveform
@ $T_J = 25^\circ\text{C}$ using CT.3

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	—	0.13	—	.005	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	7
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	7
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	6
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	6
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	4
L4	—	1.02	—	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

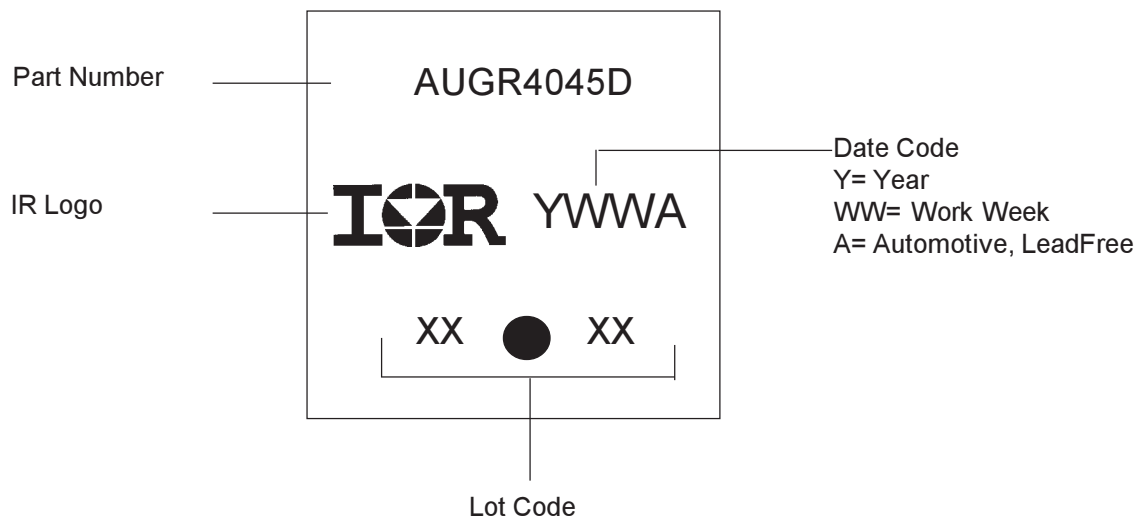
HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

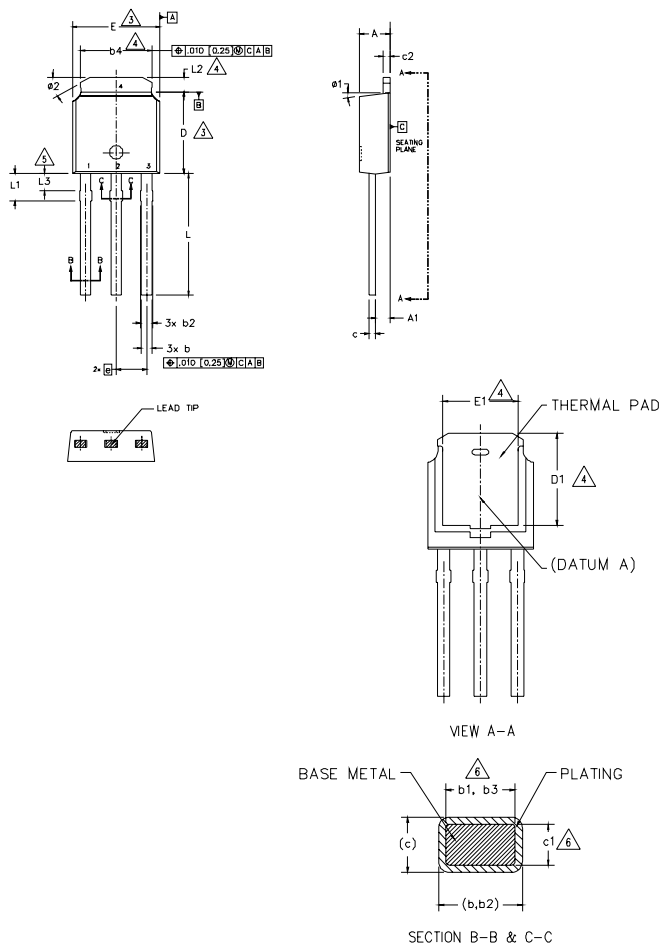
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak Part Marking Information



I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSION ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5.- LEAD DIMENSION UNCONTROLLED IN L3.
- 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
- 8.- CONTROLLING DIMENSION : INCHES.

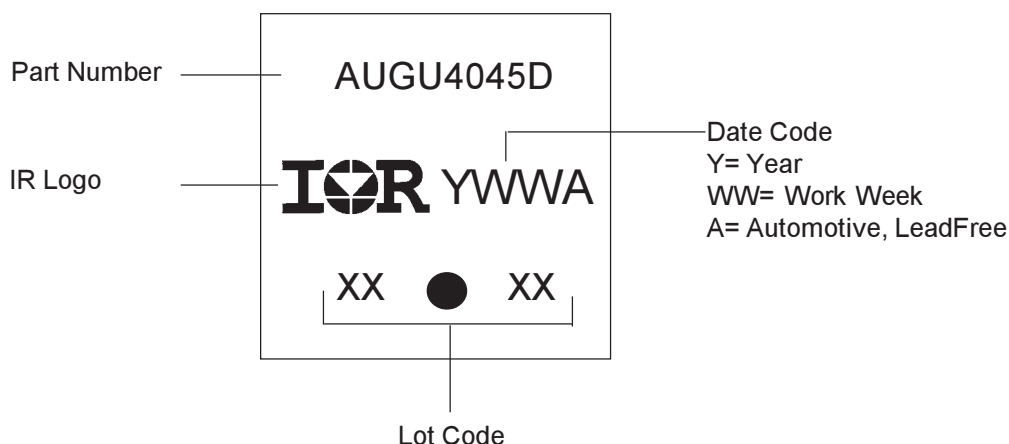
S Y M B O L	DIMENSIONS				N O T E S
	MILLIMETERS		INCHES		
			MIN.	MAX.	
A	2.18	2.39	.086	.094	6
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	
c2	0.46	0.89	.018	.035	6
D	5.97	6.22	.235	.245	
D1	5.21	—	.205	—	
E	6.35	6.73	.250	.265	3
E1	4.32	—	.170	—	
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	4
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	
L3	1.14	1.52	.045	.060	5
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

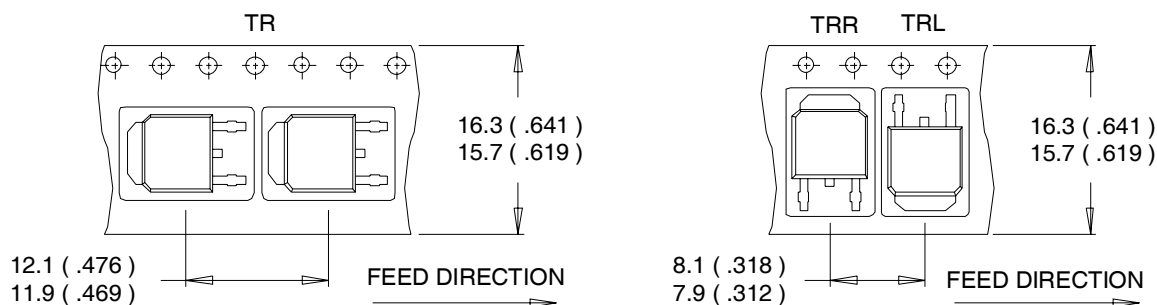
I-Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

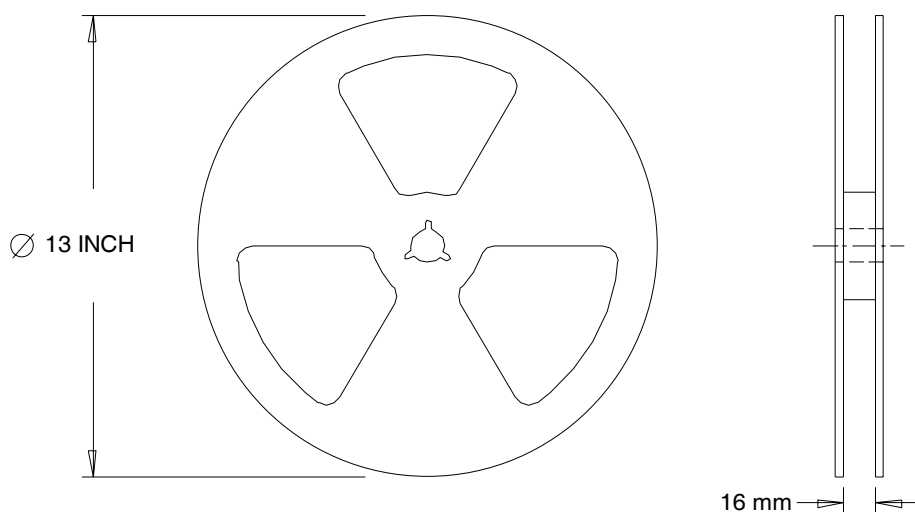
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRGR4045D	Dpak	Tube	75	AUIRGR4045D
		Tape and Reel	2000	AUIRGR4045DTR
		Tape and Reel Left	3000	AUIRGR4045DTRL
		Tape and Reel Right	3000	AUIRGR4045DTRR
AUIRGU4045D	Ipak	Tube	75	AUIRGU4045D

IMPORTANT NOTICE

Unless specifically designated for the automotive market, International Rectifier Corporation and its subsidiaries (IR) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or services without notice. Part numbers designated with the "AU" prefix follow automotive industry and / or customer specific requirements with regards to product discontinuance and process change notification. All products are sold subject to IR's terms and conditions of sale supplied at the time of order acknowledgment.

IR warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with IR's standard warranty. Testing and other quality control techniques are used to the extent IR deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

IR assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using IR components. To minimize the risks with customer products and applications, customers should provide adequate design and operating safeguards.

Reproduction of IR information in IR data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alterations is an unfair and deceptive business practice. IR is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions. Resale of IR products or serviced with statements different from or beyond the parameters stated by IR for that product or service voids all express and any implied warranties for the associated IR product or service and is an unfair and deceptive business practice. IR is not responsible or liable for any such statements.

IR products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or in other applications intended to support or sustain life, or in any other application in which the failure of the IR product could create a situation where personal injury or death may occur. Should Buyer purchase or use IR products for any such unintended or unauthorized application, Buyer shall indemnify and hold International Rectifier and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that IR was negligent regarding the design or manufacture of the product.

IR products are neither designed nor intended for use in military/aerospace applications or environments unless the IR products are specifically designated by IR as military-grade or "enhanced plastic." Only products designated by IR as military-grade meet military specifications. Buyers acknowledge and agree that any such use of IR products which IR has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR's Technical Assistance Center

<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245

Tel: (310) 252-7105